	Application No.	Applicant(s)
Notice of Allowability	10/565,108	YOSHIZAWA, KEN
	Examiner	Art Unit
	Felisa C. Hiteshew	1792
The MAILING DATE of this communication app All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85 NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT R of the Office or upon petition by the applicant. See 37 CFR 1.31.	ears on the cover sheet with the (OR REMAINS) CLOSED in this or other appropriate communical GHTS. This application is subje	te correspondence address— sapplication. If not included stron will be mailed in due course. THIS
This communication is responsive to the amendment filed.		
2. ☑ The allowed claim(s) is/are <u>5 and 7</u> .		
Acknowledgment is made of a claim for foreign priority u a) ⊠ All b) □ Some* c) □ None of the:		•
Certified copies of the priority documents have		
2. Certified copies of the priority documents have		
3. Copies of the certified copies of the priority do	cuments have been received in t	his national stage application from the
International Bureau (PCT Rule 17.2(a)).		
* Certified copies not received:		
Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONN THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.	of this communication to file a re IENT of this application.	ply complying with the requirements
4. A SUBSTITUTE OATH OR DECLARATION must be subm INFORMAL PATENT APPLICATION (PTO-152) which give	es reason(s) why the oath or dec	ER'S AMENDMENT or NOTICE OF laration is deficient.
5. CORRECTED DRAWINGS (as "replacement sheets") must		
(a) I including changes required by the Notice of Draftspers	son's Patent Drawing Review (P	TO-948) attached
1) 🗌 hereto or 2) 🔲 to Paper No./Mail Date		
(b) including changes required by the attached Examiner's Paper No./Mail Date	s Amendment / Comment or in th	e Office action of
Identifying indicia such as the application number (see 37 CFR 1 each sheet. Replacement sheet(s) should be labeled as such in t	.84(c)) should be written on the dra he header according to 37 CFR 1.1	awings in the front (not the back) of 21(d).
 DEPOSIT OF and/or INFORMATION about the depo attached Examiner's comment regarding REQUIREMENT 	sit of BIOLOGICAL MATERIA FOR THE DEPOSIT OF BIOLOG	L must be submitted. Note the GICAL MATERIAL.
Attachment(s)		
I. ☐ Notice of References Cited (PTO-892)	5. Notice of Informa	al Patent Application
. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948)	6. Interview Summa	ary (PTO-413), .
. ☐ Information Disclosure Statements (PTO/SB/08), Paper No./Mail Date	7. Examiner's Ame	
 Examiner's Comment Regarding Requirement for Deposit of Biological Material 	8. Examiner's State	ment of Reasons for Allowance
	9. Other	
		/Felisa C. Hiteshew/ Primary Examiner Art Unit: 1792
U.S. Patent and Trademark Office		Primary Examiner Art Unit: 1792

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EXAMINER'S AMENDMENT

An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

The application has been amended as follows:

In the specification, on page 1, between the title and the first paragraph, insert the following paragraph:

--This application is a national stage application of International Application No. $PCT/JP2004/09921 \ filed \ July \ 12, \ 2004--.$

In the claims: Please cancel claims 9 and 11.

1. The following is an examiner's statement of reasons for allowance: The most relevant prior art of reference is that of U.S. Patent No. 6,086,070 A and U.S. Patent Application Publication US2004/0072347 A1. However, it does not teach nor fairly suggest singularly or in any combination thereof a method for producing a silicon wafer having a crystal orientation <110> from a silicon single crystal ingot grown by Floating Zone method (FZ method), wherein, at least, an FZ silicon single crystal ingot is grown by being made to be dislocation-free by Dash Necking method using a seed crystal having its crystal axis inclined at a specified angle from a crystal orientation <110>, and the grown FZ silicon single crystal ingot is sliced at the just angle of a crystal orientation <110> to produce a silicon wafer having a crystal orientation <110>, and the sliced

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silicon wafer having a crystal orientation <110> is made to be a perfect circle by processing of chamfering.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Felisa C. Hiteshew whose telephone number is (571) 272-1463. The examiner can normally be reached on Mon-Thurs 5:30a.m. -4 p.m.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Michael Barr can be reached on (571) 272-1414. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

/Felisa C. Hiteshew/ Primary Patent Examiner Art Unit 1792